



Substitute for Form 1449A/PTO
**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**
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		Complete If Known	
		Application Number	10/763136
		Filing Date	January 22, 2004
		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown
		Examiner Name	Nguyen, Tuan
Sheet 1 of 4		Attorney Docket No: 303.588US3	

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Substitute Disclosure Statement Form (PTO-1449)

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